# HERMETIC SCHOTTKY RECTIFIER <br> Very Low Forward Voltage Drop 

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

| Characteristics | Symbol | Condition | Max. | Units |
| :---: | :---: | :---: | :---: | :---: |
| Peak Inverse Voltage | $\mathrm{V}_{\text {RWM }}$ | - | 60 | V |
| Max. Average Forward Current | $\mathrm{I}_{\text {(AV) }}$ | 50\% duty cycle, rectangular wave form (Single) | 60 | A |
| Max. Average Forward Current | $\mathrm{I}_{\text {(AV) }}$ | 50\% duty cycle, rectangular wave form (Common Cathode) | 60 | A |
| Max. Peak One Cycle NonRepetitive Surge Current | $\mathrm{I}_{\text {FSM }}$ | 8.3 ms , half Sine wave (per leg) | 860 | A |
| Non-Repetitive Avalanche Energy | $\mathrm{E}_{\text {AS }}$ | $\begin{aligned} & \mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}, \mathrm{I}_{\mathrm{AS}}=3.0 \mathrm{~A}, \\ & \mathrm{~L}=4.4 \mathrm{mH} \text { (per leg) } \\ & \hline \end{aligned}$ | 20 | mJ |
| Repetitive Avalanche Current | $\mathrm{I}_{\text {AR }}$ | $\mathrm{I}_{\mathrm{AS}}$ decay linearly to 0 in $1 \mu \mathrm{~S}$ $f$ limited by $\mathrm{T}_{\mathrm{J}} \max \mathrm{V}_{\mathrm{A}}=1.5 \mathrm{~V}_{\mathrm{R}}$ | 3.0 | A |
| Maximum Thermal Resistance | $\mathrm{R}_{\text {өJС }}$ | DC operation | 0.35 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Max. Junction Temperature | TJ | - | -65 to +175 | ${ }^{\circ} \mathrm{C}$ |
| Max. Storage Temperature | $\mathrm{T}_{\text {stg }}$ | - | -65 to +175 | ${ }^{\circ} \mathrm{C}$ |

## Electrical Characteristics

| Characteristics | Symbol | Condition | Max. | Units |
| :---: | :---: | :---: | :---: | :---: |
| Max. Forward Voltage Drop (per leg) | $\mathrm{V}_{\text {F1 }}$ | @ 60A, Pulse, $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ | 0.66 | V |
|  | $\mathrm{V}_{\mathrm{F} 2}$ | @ 60A, Pulse, $\mathrm{T}_{\mathrm{J}}=125^{\circ} \mathrm{C}$ | 0.59 | V |
| Max. Reverse Current (per leg) | $\mathrm{I}_{\mathrm{R} 1}$ | $\begin{aligned} & @ V_{R}=60 \mathrm{~V}, \text { Pulse, } \\ & \mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C} \end{aligned}$ | 1.2 | mA |
|  | $\mathrm{I}_{\mathrm{R} 2}$ | $\begin{aligned} & \begin{array}{\|l} @ V_{R}=60 \mathrm{~V}, \text { Pulse, } \\ T_{J}=125^{\circ} \mathrm{C} \\ \hline \end{array} \\ & \hline \end{aligned}$ | 90 | mA |
| Max. Junction Capacitance (per leg) | $\mathrm{C}_{\text {T }}$ | $\begin{aligned} & @ V_{\mathrm{R}}=5 \mathrm{~V}, \mathrm{~T}_{\mathrm{C}}=25^{\circ} \mathrm{C} \\ & \mathrm{f}_{\mathrm{SIIG}}=1 \mathrm{MHz}, \\ & \mathrm{~V}_{\mathrm{SIG}}=50 \mathrm{mV}(\mathrm{p}-\mathrm{p}) \\ & \hline \end{aligned}$ | 2600 | pF |

## MECHANICAL DIMENSIONS: In Inches / mm



Note: The $V_{f}$ curves shown are for the SD200SB60 unpackaged die only.


## TECHNICAL DATA


#### Abstract

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